



DMTH6002LPS

60V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8 (Type K)

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C (Note 9)
	2mΩ @ V _{GS} = 10V	100A
60V	3mΩ @ V _{GS} = 6V	100A
	$3.3 \text{m}\Omega @ V_{GS} = 4.5 \text{V}$	100A

Features

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- Thermally Efficient Package Cooler Running Applications
- High Conversion Efficiency
- Low R_{DS(ON)} Minimizes On-State Losses
- <1.1mm Package Profile Ideal for Thin Applications
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

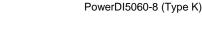
Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Switching
- Synchronous Rectification
- DC-DC Converters

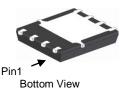
Mechanical Data

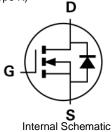
- Case: PowerDI[®]5060-8 (Type K)
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.097 grams (Approximate)

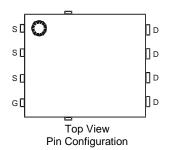




Top View







Ordering Information (Note 4)

Part Number	Case	Packaging	
DMTH6002LPS-13	PowerDI5060-8 (Type K)	2,500 / Tape & Reel	

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead_free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website athttps://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



D' | = Manufacturer's Marking TH6002LS = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 18 = 2018) WW = Week Code (01 to 53)

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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V_{DSS}	60	V	
Gate-Source Voltage		V _{GSS}	±20	V
Continuous Prain Current // 10\/ (Notes 6.8.0)	T _C = +25°C	1	100	A
Continuous Drain Current, V _{GS} = 10V (Notes 6 & 9)	$T_C = +100^{\circ}C$	ID	100	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I _{DM}	400	Α
Continuous Body Diode Forward Current (Note 6)	T _C = +25°C	Is	100	Α
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)		I _{SM}	400	Α
Avalanche Current, L = 3mH		I _{AS}	14	Α
Avalanche Energy, L = 3mH		E _{AS}	294	mJ

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_{D}	2.3	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	55	°C/W
Total Power Dissipation (Note 6)	P _D	167	W
Thermal Resistance, Junction to Case (Note 6)	$R_{\theta JC}$	0.9	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

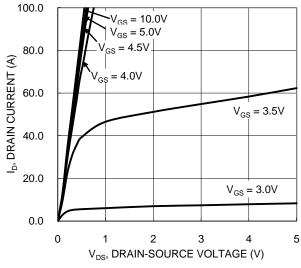
Characteristic	Symbol	Min	Tym	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)	Syllibol	IVIIII	Тур	IVIAX	Onit	rest Condition	
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	_			1	μA	$V_{DS} = 48V, V_{GS} = 0V$	
Gate-Source Leakage	I _{DSS}			±100	nA		
ON CHARACTERISTICS (Note 7)	I_{GSS}			±100	ПΛ	$V_{GS} = \pm 20V, V_{DS} = 0V$	
Gate Threshold Voltage	V	1	_	3	V	V-0 - V00 I 250uA	
Gate Tilleshold Voltage	V _{GS(TH)}		1.7	2	v	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Busin Source On Bosistance	_				0	$V_{GS} = 10V, I_D = 30A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	2	3	mΩ	$V_{GS} = 6V$, $I_D = 30A$	
		_	2.3	3.3		$V_{GS} = 4.5V, I_D = 30A$	
Diode Forward Voltage	V_{SD}	_	_	1.2	V	$V_{GS} = 0V, I_{S} = 50A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	1	6555	_		$V_{DS} = 30V$, $V_{GS} = 0V$, $f = 1MHz$	
Output Capacitance	Coss	-	2264	_	pF		
Reverse Transfer Capacitance	Crss	_	187	_			
Gate Resistance	Rq	-	0.7	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 10V)	Qg		130.8	_			
Total Gate Charge (V _{GS} = 4.5V)	Qq	-	63.6	_		$V_{DS} = 30V, I_{D} = 50A$	
Gate-Source Charge	Q _{gs}	-	20.8	_	nC		
Gate-Drain Charge	Q_{gd}	_	29.4	_			
Turn-On Delay Time	t _{D(ON)}	_	11.2	_		$V_{DD} = 20V, V_{GS} = 10V,$ $I_{D} = 50A, R_{g} = 2.5\Omega$	
Turn-On Rise Time	t _R		10.8	_	20		
Turn-Off Delay Time	t _{D(OFF)}	_	44	_	ns		
Turn-Off Fall Time	t _F	ı	19.5	_			
Reverse Recovery Time	t _{RR}	-	61.8	_	ns	L = 50A di/dt = 100A/us	
Reverse Recovery Charge	Q_{RR}	_	123	_	$I_F = 50A$, di/dt = 100A/ μ s		

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

^{6.} Thermal resistance from junction to soldering point (on the exposed drain pad).7. Short duration pulse test used to minimize self-heating effect.

Guaranteed by design. Not subject to product testing.
 Package limited.







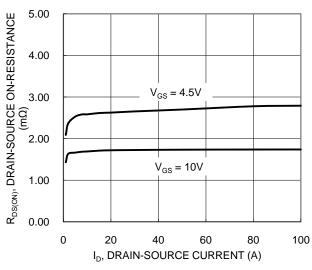


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

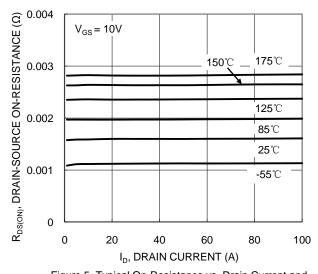


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

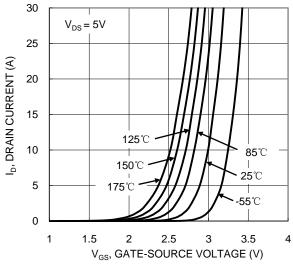


Figure 2. Typical Transfer Characteristic

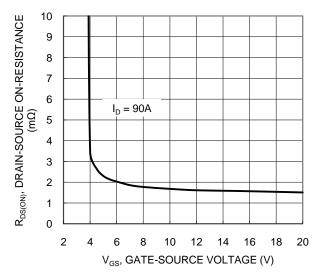


Figure 4. Typical Transfer Characteristic

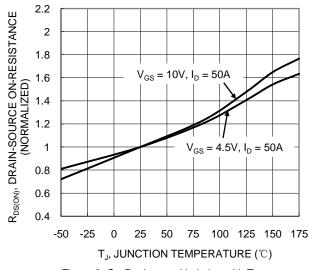


Figure 6. On-Resistance Variation with Temperature



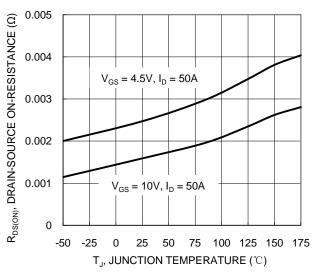


Figure 7. On-Resistance Variation with Temperature

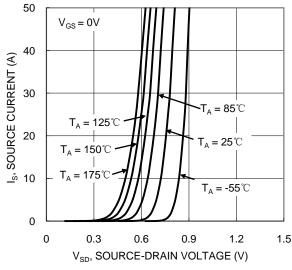
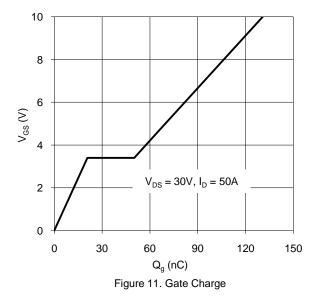


Figure 9. Diode Forward Voltage vs. Current



2.4 $V_{GS(TH)}, \text{ GATE THRESHOLD VOLTAGE (V)}$ 2.2 2 $I_D = 1mA$ 1.8 1.6 1.4 $I_{D} = 250 \mu A$ 1.2 1 0.8 0.6

0.4

-50

-25

0

25 50

T_.I, JUNCTION TEMPERATURE (°C) Figure 8. Gate Threshold Variation vs. JunctionTemperature

75

100 125 150 175

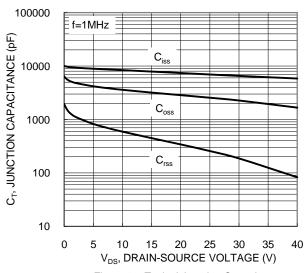


Figure 10. Typical Junction Capacitance

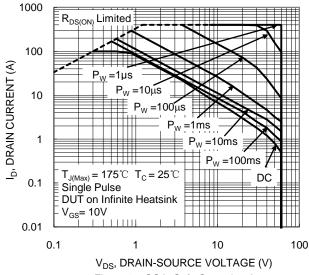


Figure 12. SOA, Safe Operation Area



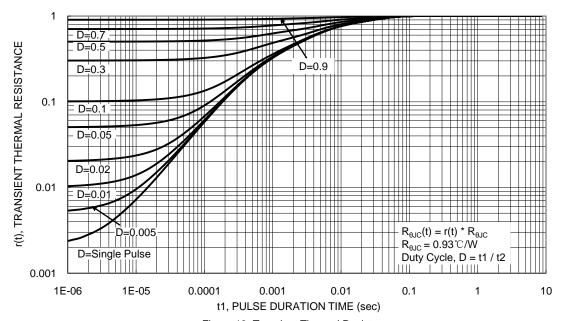


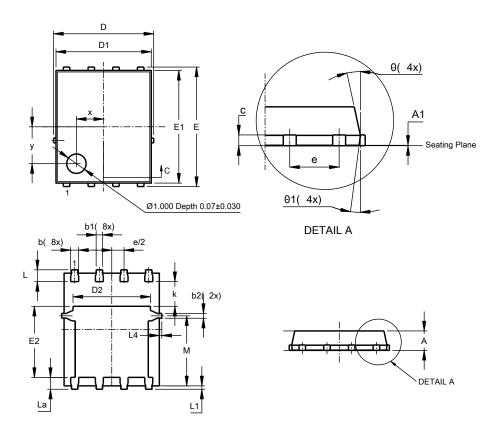
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (Type K)

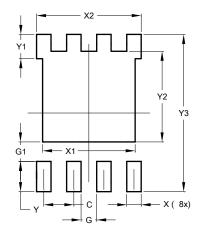


PowerDI5060-8					
(Type K)					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A1	0	0.05	0.02		
b	0.33	0.51	0.41		
b1	0.300	0.366	0.333		
b2	0.20	0.35	0.25		
С	0.23	0.33	0.277		
D	5	.15 BS0	2		
D1	4.85	4.95	4.90		
D2	-		3.98		
Е	_	.15 BS0	3		
E1	5.75	5.85	5.80		
E2	3.56	3.725	3.66		
е		.27BSC			
k	-		1.27		
L	0.51	0.71	0.61		
La	0.51	0.675	0.61		
L1	0.05	0.20	0.175		
L4	-	-	0.125		
М	3.50	3.71	3.605		
Х	-	-	1.400		
у	-	-	1.900		
θ	10°	12°	11°		
θ1	6°	8°	7°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (Type K)



Dimensions	Value (in mm)		
С	1.270		
G	0.660		
G1	0.820		
X	0.610		
X1	3.910		
X2	4.420		
Y	1.270		
Y1	1.020		
Y2	3.810		
Y3	6.610		



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